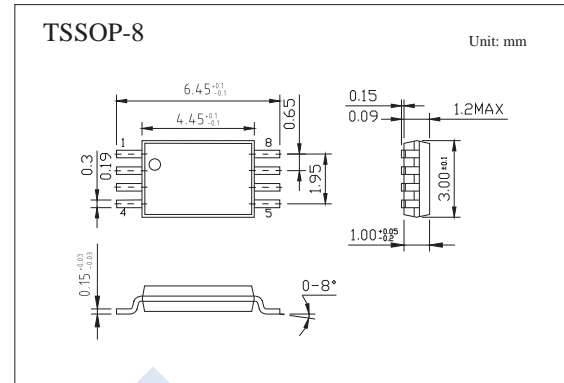
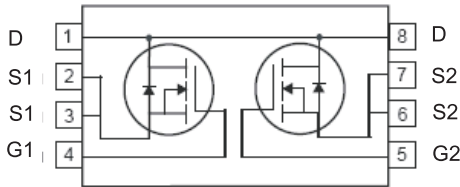


Dual N-Channel Enhancement MOSFET

KI8205A

■ Features

- 6.5 A, 20 V. $R_{DS(on)} = 0.025\Omega$ @ $V_{GS} = 4.5$ V
 $R_{DS(on)} = 0.029\Omega$ @ $V_{GS} = 2.5$ V.

■ Absolute Maximum Ratings $T_A = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V_{DS}	20	V	
Gate-Source Voltage	V_{GS}	± 12	V	
Continuous Drain Current	I_D	6.5	A	
Pulsed Drain Current (1)	I_{DM}	20	A	
Maximum Power Dissipation	P_D	$T_A = 25^\circ\text{C}$	1.6	W
		$T_A = 70^\circ\text{C}$	0.7	W
Thermal Resistance, Junction-to-Ambient (2)	$R_{\theta JA}$	78	$^\circ\text{C}/\text{W}$	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	40	$^\circ\text{C}/\text{W}$	
Junction temperature and Storage temperature	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$	

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.

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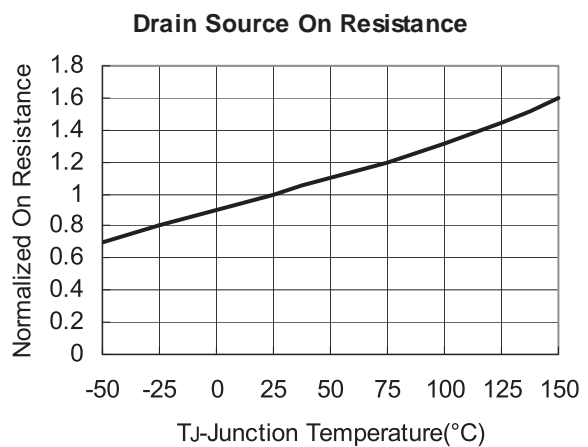
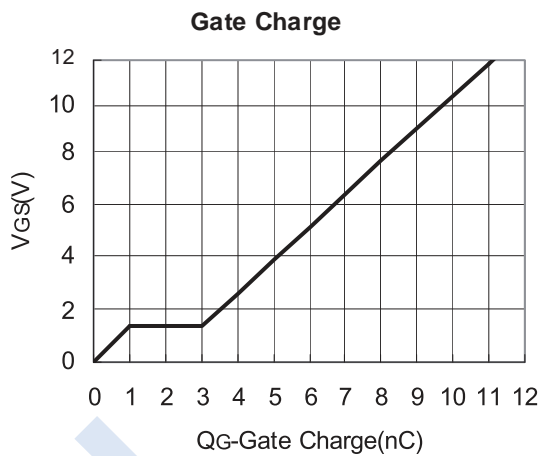
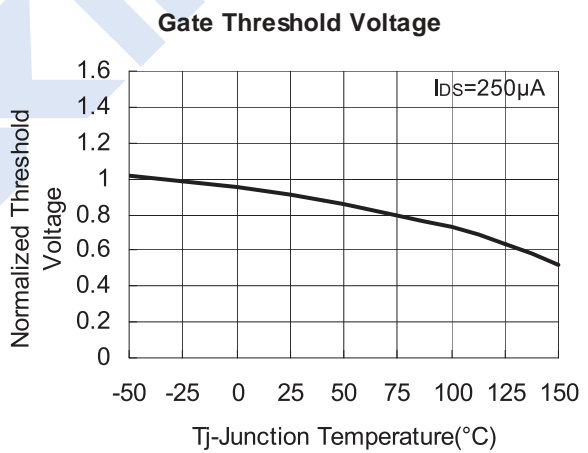
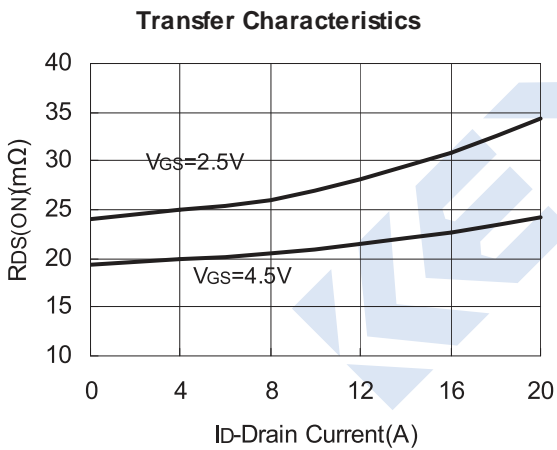
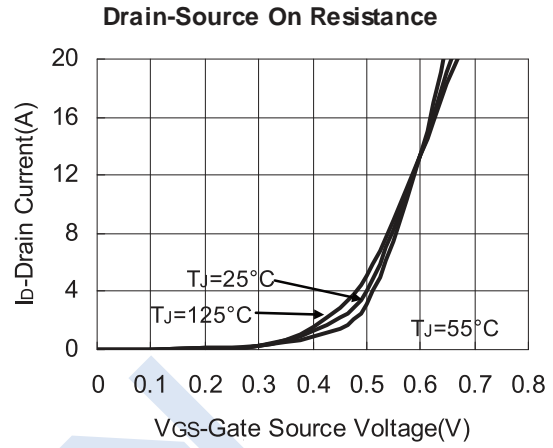
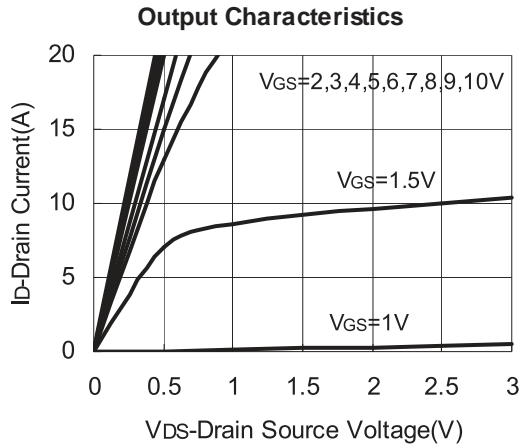
■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	V _{GS} = 0 V, I _D = 250 μA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V			1	uA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 55°C			5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±12V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250uA	0.5	1	1.5	V
Drain-Source On-State Resistance *	r _{DSON}	V _{GS} = 4.5V, I _D = 6.5A			0.025	Ω
		V _{GS} = 2.5V, I _D = 5.4A			0.029	
On-State Drain Current *	I _{D(on)}	V _{DS} = 5V, V _{GS} = 4.5V	15			A
Forward Transconductance *	g _{fs}	V _{DS} = 5V, I _D = 3A		11		S
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1.0 MHz		700		pF
Output Capacitance	C _{oss}			175		pF
Reverse Transfer Capacitance	C _{rss}			85		pF
Total Gate Charge	Q _g			7	10	nC
Gate-Source Charge	Q _{gs}	V _{DS} = 10V, V _{GS} = 4.5V, I _D = 3A		1.2		
Gate-Drain Charge	Q _{gd}			1.9		
Turn-On Delay Time	t _{d(on)}			8	16	ns
Rise Time	t _r	V _{DD} = 10V		10	18	
Turn-Off Delay Time	t _{d(off)}	I _D = 1A, V _{GS} = 4.5V, R _G = 6 Ω		18	29	
Fall Time	t _f			5	10	
Maximum Continuous Drain-Source Diode Forward Current	I _S				1.3	A
Diode Forward Voltage *	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V		0.65	1.2	V

* Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

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■ Typical Characteristics



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